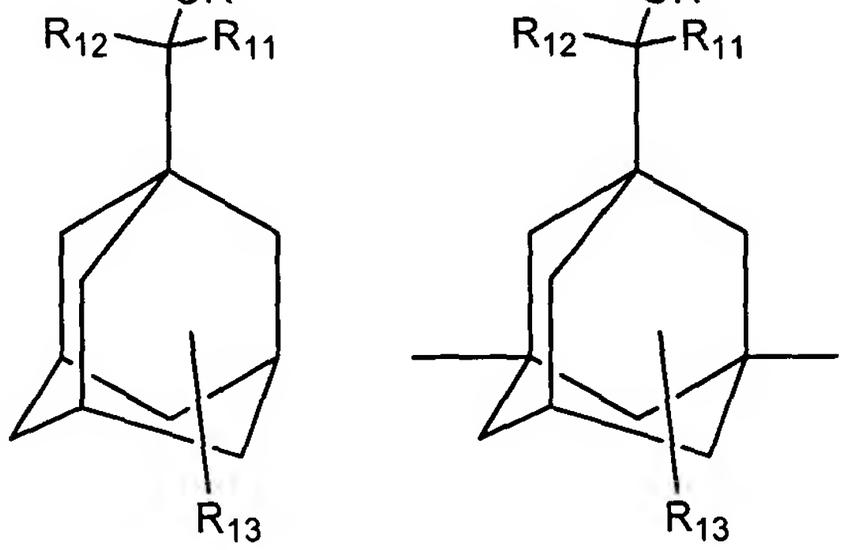
AMENDMENTS TO THE CLAIMS

Please amend the claims as follows:

1. – 29. (Canceled)

30. (New) A process for producing a semiconductor device, comprising the steps of:

forming, on an etching film formed on a substrate, a film containing a resist composition which comprises a resist resin obtained by homopolymerizing at least one monomer selected from monomers represented by the general formulas (I-1) and (I-2):



(I-1)

(I-2)

wherein R is acryloyl or methacryloyl group, R_{11} and R_{12} are hydrogen atom or a monovalent alkyl group, with proviso that at least one of R_{11} and R_{12} is monovalent alkyl group, and R_{13} is OH group, =O group, COOH group or $COOR_{14}$ group, wherein R_{14} is a monovalent organic group, or by copolymerizing the monomer(s) and any other vinyl monomer, and a photo acid generator,

subjecting the film coated onto the substrate to pattern-wise exposure,

developing the film exposed to light, thereby forming a patterned photomask, and

etching an etching film by dry etching, using the photomask as a mask.

31. (New) The process for producing a semiconductor device according to claim 30, wherein the monovalent alkyl group is selected from the group consisting of methyl, ethyl, propyl, and iso-propyl groups.

32. (New) The process for producing a semiconductor device according to claim 30, wherein both R_{11} and R_{12} are monovalent alkyl groups.

33. (New) The process for producing a semiconductor device according to claim 32, wherein the monovalent alkyl group is selected from the group consisting of methyl, ethyl, propyl, and iso-propyl groups.

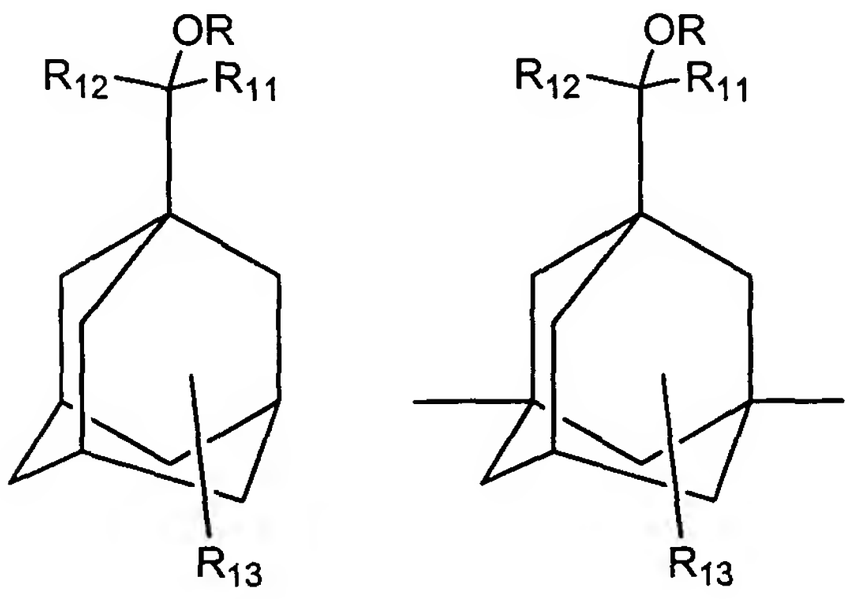
34. (New) The process for producing a semiconductor device according to claim 30, wherein R_{13} is =O group.

35. (New) The process for producing a semiconductor device according to claim 30, wherein at least one of R_{11} and R_{12} contained in the resist resin is selected from the group consisting of C_2H_5 group, C_3H_7 group and C_4H_9 group.

36. (New) The process for producing a semiconductor device according to claim 30, wherein R_{13} is combined with a tertiary carbon atom.

37. (New) A resist composition comprising:

a resist resin obtained by copolymerizing at least one monomer selected from monomers represented by the general formulas (I-1) and (I-2):

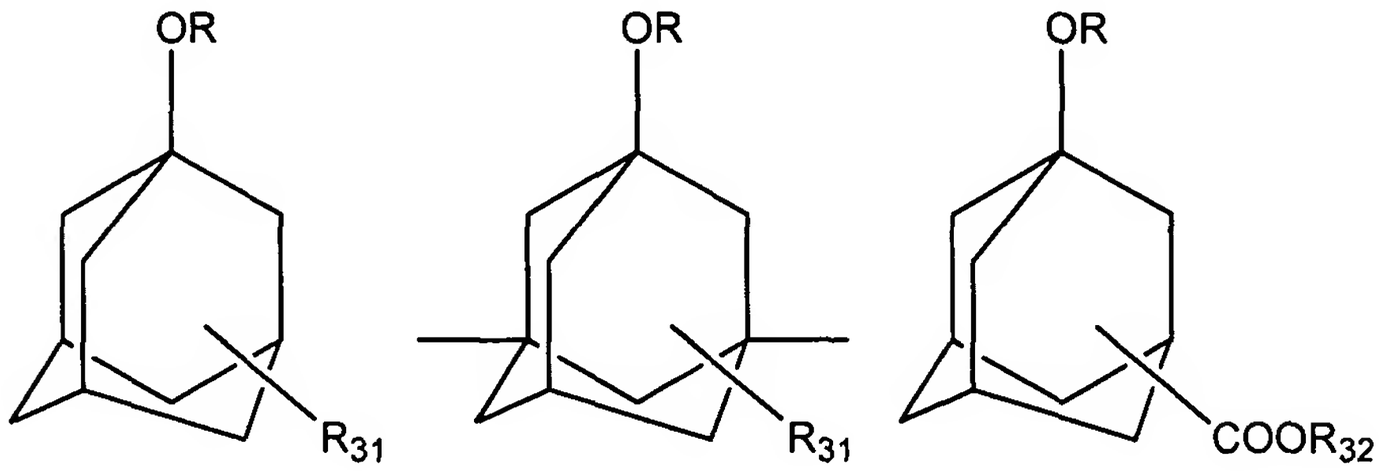


(I-1) (I-2)

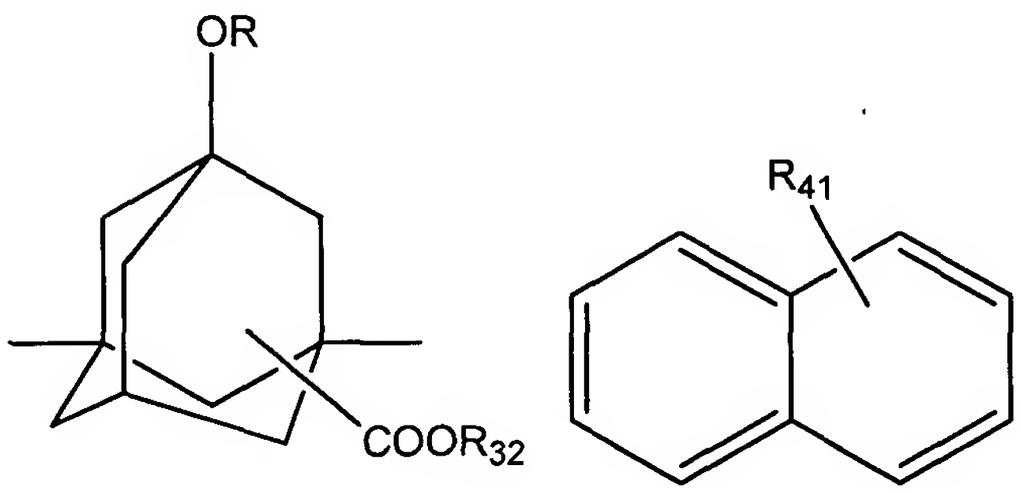
wherein R is acryloyl or methacryloyl group, R_{11} and R_{12} are hydrogen atom or a monovalent alkyl group, with proviso that at least one of R_{11} and R_{12} is monovalent alkyl

group, and R_{13} is OH group, =O group, COOH group or $COOR_{14}$ group, wherein R_{14} is a monovalent organic group,

and at least one monomer selected from monomers represented by the general formulas (I-3), (I-4), (I-5), (I-6) and (I-7):



(I-3) (I-4) (I-5)



(I-6) (I-7)

wherein R_{31} is hydrogen atom, or at least one group selected from the group consisting of OH group, OR_{14} group, wherein R_{14} is a monovalent organic group, and =O group, R_{32} is hydrogen atom or a monovalent organic group, and R_{41} is a vinyl, acryloyl or methacryloyl group; and

a photo acid generator.

38. (New) A resist composition according to claim 37, wherein the monovalent alkyl group is selected from the group consisting of methyl, ethyl, propyl, and iso-propyl groups.

39. (New) A resist composition according to claim 37, wherein both R_{11} and R_{12} are monovalent alkyl groups.

40. (New) A resist composition according to claim 39, wherein the monovalent alkyl group is selected from the group consisting of methyl, ethyl, propyl, and iso-propyl groups.

41. (New) A pattern forming process comprising the steps of:

forming, on a substrate, a film containing the resist composition set forth in claim 37,

subjecting the film to pattern-wise exposure, and

developing the film exposed to light.